

ABSTRACT

Silver electrode metallization in light emitting devices is subject to electrochemical migration in the presence of moisture and an electric field. Electrochemical migration of the silver metallization to the pn junction of the device results in an alternate shunt path across the junction, which degrades efficiency of the device. In accordance with a form of this invention, a migration barrier is provided for preventing migration of metal from at least one of the electrodes onto the surface of the semiconductor layer with which the electrode is in contact.